



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

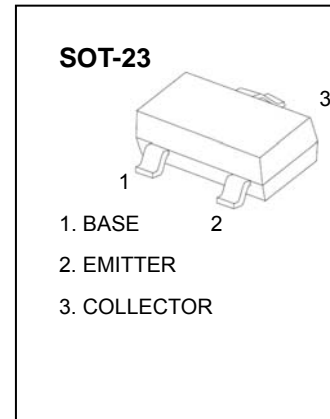
2SA1037 TRANSISTOR (PNP)

FEATURES

- Excellent h_{FE} linearity.
- Compliments the 2SC2412

MARKING : FQ, FR, FS

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)



Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-60	V
V_{CE0}	Collector-Emitter Voltage	-50	V
V_{EB0}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12\text{V}, I_C=-2\text{mA}, f=30\text{MHz}$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12\text{V}, I_E=0, f=1\text{MHz}$		4.0	5.0	pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120 - 270	180 - 390	270 - 560

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Typical Characteristics

2SA1037

